

# Transistor Amplifier

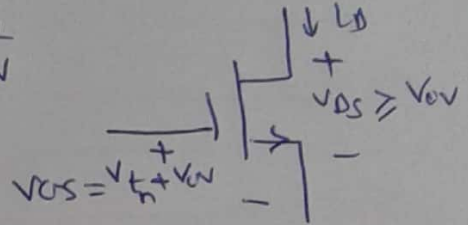
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## 7.1 Basic Amplifier operations

It operates in saturation region

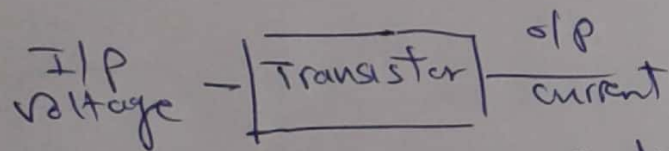
$$\begin{aligned} V_{DS} &\geq V_{GS} - V_{tn} \\ \text{or } V_{DS} &\geq V_{OV} \\ \text{or } V_{GD} &\leq V_{tn} \end{aligned}$$

$$\begin{aligned} I_D &= \frac{1}{2} K_n [V_{GS} - V_{tn}]^2 \\ &= \frac{1}{2} K_n V_{OV}^2 = \frac{1}{2} K_n \frac{W}{L} V_{OV}^2 \\ &= \frac{1}{2} \mu_n C_{ox} \frac{W}{L} (V_{GS} - V_{tn})^2 \end{aligned}$$



$I_D$  is independent on  $V_{DS}$

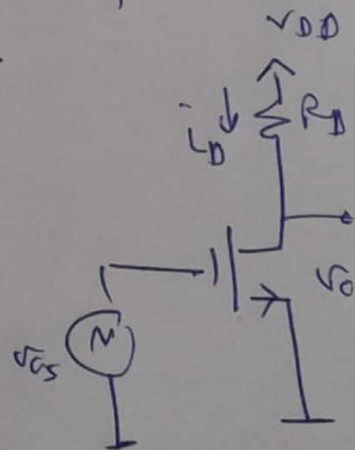
## 7.1.2. Obtaining a voltage Amplifier

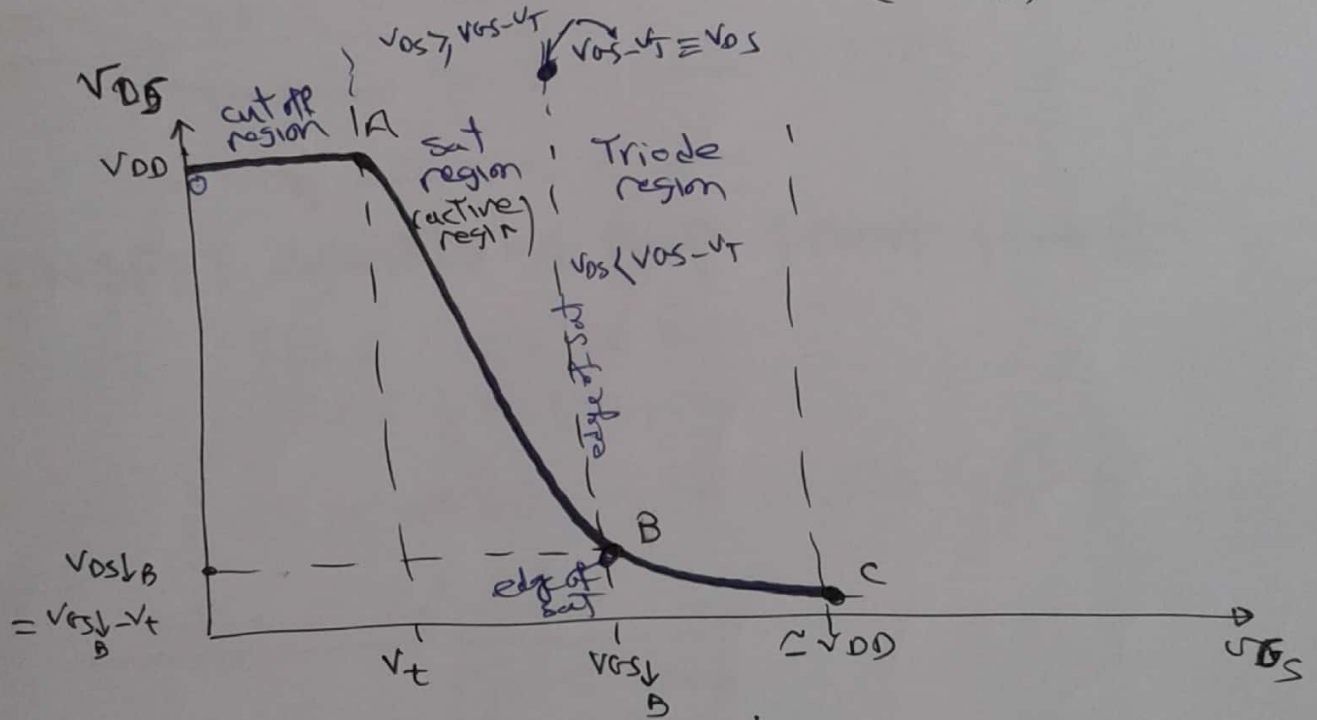
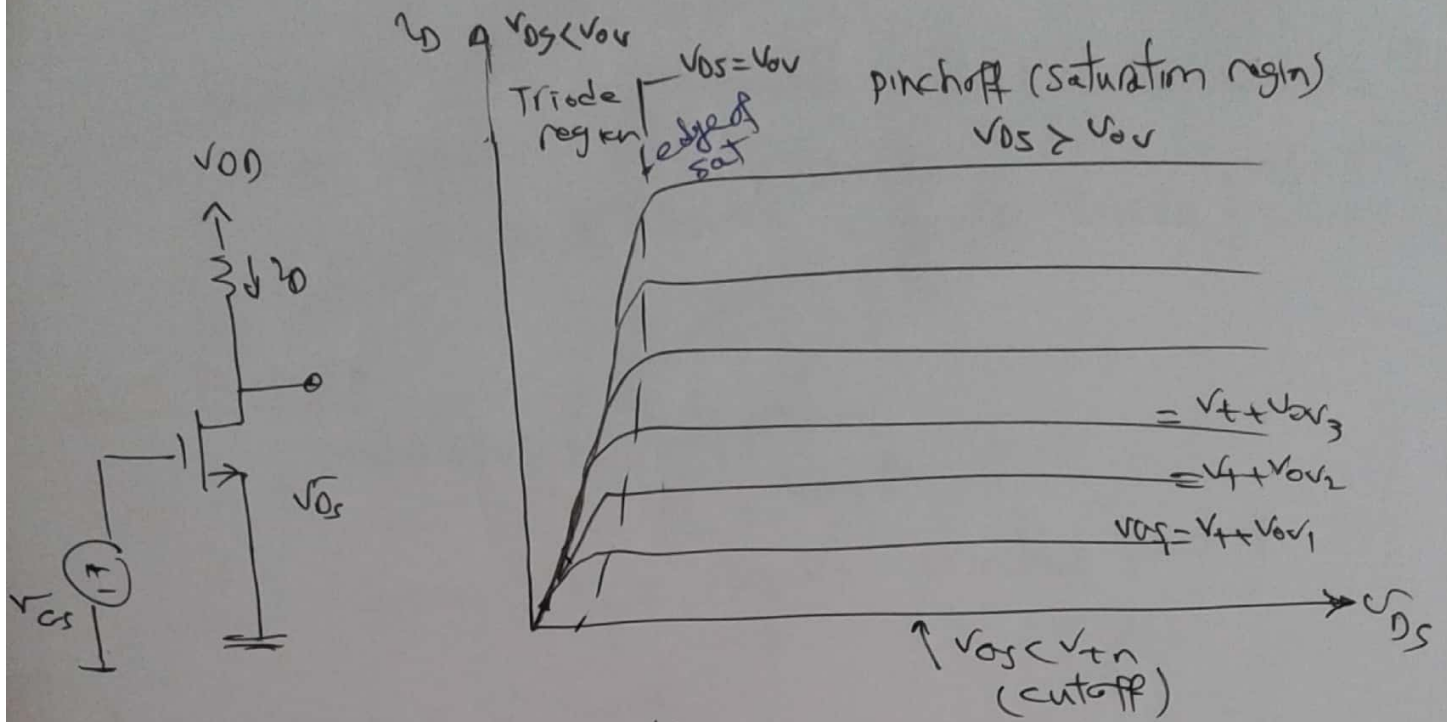


So it is basically Trans conductance amplifier  
To convert Trans conductance amplifier to voltage amplifier, we need to pass output current through a resistor at o/p.

$$V_{DS} \equiv V_o = V_{DD} - I_D R_D$$

when  $I_D = 0$   
 $\therefore V_o = V_{DD}$





### 7.1.3 Voltage-Transfer characteristics

Transfer characteristics:  $V_{DS}$  vs  $V_{GS}$   
 The relationship between  $V_{GS}$  and  $V_{DS}$  is given by:  

$$V_{GS} - V_{th} = V_{GS} - V_{th} \Rightarrow V_{GS} = V_{GS} - V_{th}$$

- 1 From 0 → A:  $V_{GS} < V_{th} \Rightarrow I_D = 0 \quad V_{DS} = V_{DD}$
- 2 A-B as  $V_{GS}$  exceeds  $V_{th}$  Transistor will be on,  $R_D$  is present  

$$V_{DS} = V_{DD} - I_D R_D$$
- as  $I_D \uparrow \quad V_{DS} \downarrow$
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Transistor still in saturation until  $V_{DS}$  become less than  $V_{GS} - V_T$   
 at  $V_{DS} \leq V_{GS} - V_T$  \* start to go to Triode [edge of Saturation]

from A  $\rightarrow$  B

Transistor in saturation  
 $V_{DS} \downarrow$ ,  $V_{GS} \uparrow$

when  $V_{DS_B} = V_{GS_B} - V_T$  reached point B

when  $V_{DS} < V_{GS} - V_T$

transistor go to triode region

so  $V_{DS}$  decrease slowly

# MOSFET operates as Amp from A  $\rightarrow$  B

$$\therefore V_{DS} = V_{DD} - I_D R_D$$

$$I_D = \frac{1}{2} K_n (V_{GS} - V_T)^2$$

$$\therefore V_{DS} = V_{DD} - \frac{1}{2} K_n R_D (V_{GS} - V_T)^2 \rightarrow \text{[1]}$$

at edge of saturation (B)

$$V_{GS} \equiv V_{GS_B}$$

$$\therefore V_{DS} = V_{GS} - V_T \quad \text{so } V_{DS_B} = V_{GS_B} - V_T$$

sub into eq ①

$$V_{DS_B} = V_{GS_B} - V_T = V_{DD} - \frac{1}{2} K_n R_D (V_{GS_B} - V_T)^2$$

$$V_{GS_B} - V_T = V_{DD} - \frac{1}{2} K_n R_D [V_{GS_B}^2 - 2V_{GS_B}V_T + V_T^2]$$

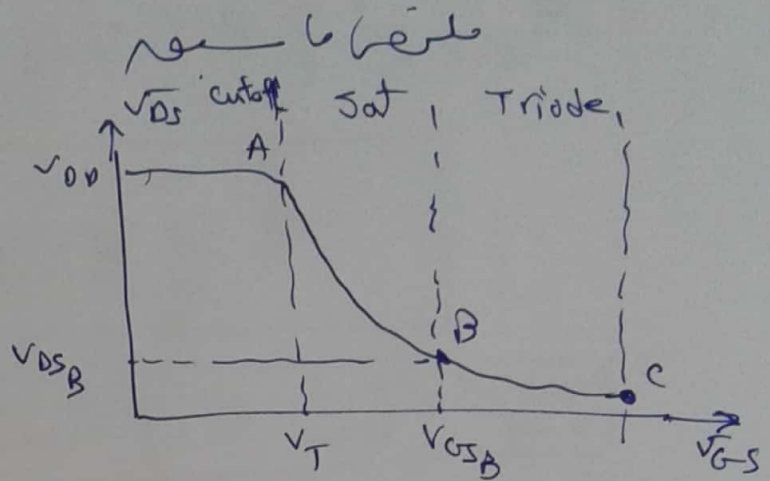
$$\therefore \frac{1}{2} K_n R_D [V_{GS_B}^2 - 2V_{GS_B}V_T + V_T^2] + V_{GS_B} - (V_T + V_{DD}) = 0$$

$$\therefore V_{GS_B}^2 - 2V_{GS_B}V_T + V_T^2 + \frac{V_{GS_B}}{\frac{1}{2} K_n R_D} - \frac{(V_T + V_{DD})}{\frac{1}{2} K_n R_D} = 0$$

①  $0 \rightarrow A$  Cutoff  
 $v_{DS} = v_{DD}$ ,  $I_D = 0$

②  $A \rightarrow B$  Sat  
 $I_D = \frac{1}{2} k_n \frac{W}{L} [v_{GS} - v_T]^2$

at edge of Sat  
 ~~$v_{GS} = v_{GSB}$~~



③ at edge of Sat  
 $v_{GSB} \approx v_T + \frac{\sqrt{2v_{DD}k_nR_D + 1} - 1}{k_nR_D}$

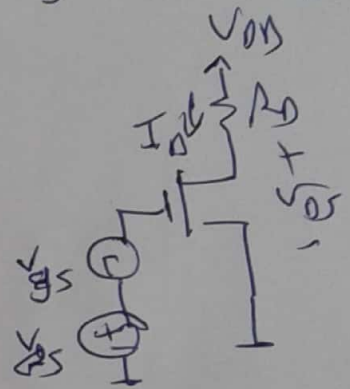
$v_{DSB} = v_{GSB} - v_T \approx \frac{\sqrt{2v_{DD}k_nR_D + 1} - 1}{k_nR_D}$

③ From B - C Triode

$I_D = k_n \frac{W}{L} \left[ (v_{GS} - v_T)v_{DS} - \frac{v_{DS}^2}{2} \right]$

$v_{DS} = v_{DD} - \frac{I_D R_D}{\text{Triode}}$

$v_{DS} = v_{DD} - R_D k_n \frac{W}{L} \left[ (v_{GS} - v_T)v_{DS} - \frac{v_{DS}^2}{2} \right]$



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$$\therefore \overset{a}{\sqrt{v_{GSB}}^2} - \left( \overset{b}{2V_t} - \frac{2}{knR_D} \right) \sqrt{v_{GSB}} - \frac{2(V_t + V_{DD})}{knR_D} = 0$$

$$\boxed{\begin{aligned} ax^2 + bx + c &= 0 \\ x &= \frac{-b \pm \sqrt{b^2 - 4ac}}{2a} \end{aligned}}$$

$$\therefore \sqrt{v_{GSB}} = \frac{\left( 2V_t - \frac{2}{knR_D} \right) \pm \sqrt{\left( 2V_t - \frac{2}{knR_D} \right)^2 + \frac{8(V_t + V_{DD})}{knR_D}}}{2}$$

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$$M = \left( 2V_t - \frac{2}{knR_D} \right)^2 + \frac{8(V_t + V_{DD})}{knR_D}$$

$$= 4V_t^2 - \frac{8V_t}{knR_D} + \frac{4}{kn^2R_D^2} + \frac{8(V_t + V_{DD})}{knR_D}$$

$$= 4V_t^2 - \frac{8V_t}{knR_D} + \frac{4}{kn^2R_D^2} + \frac{8V_t}{knR_D} + \frac{8V_{DD}}{knR_D}$$

$$= 4V_t^2 + \frac{4}{kn^2R_D^2} + \frac{8V_{DD}}{knR_D}$$

$$= 4 \left[ V_t^2 + \frac{2V_{DD}}{knR_D} + \frac{1}{(knR_D)^2} \right]$$

when neglect  $V_t$  since it is very small ( $V_t^2$  can be neglected)

$$\therefore M \approx 4 \left[ \frac{2V_{DD}}{knR_D} + \frac{1}{(knR_D)^2} \right]$$

$$\approx 4 \left[ \frac{2V_{DD}knR_D + 1}{(knR_D)^2} \right]$$

( $knR_D$ )<sup>2</sup> 1

$$\therefore \sqrt{v_{GSB}} \approx \frac{\left( 2V_t - \frac{2}{knR_D} \right) \pm \sqrt{M}}{2}$$

$$\approx V_t - \frac{1}{knR_D} \pm \frac{1}{2} \sqrt{\frac{4(2V_{DD}knR_D + 1)}{(knR_D)^2}}$$

edge in of saturation  $\sqrt{v_{GSB}} \approx V_t - \frac{1}{knR_D} \pm \frac{1}{knR_D} \sqrt{2V_{DD}knR_D + 1}$

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Since region from B to C by Triode

$$\therefore I_D = k_n \left[ (V_{GS} - V_t) V_{DS} - \frac{V_{DS}^2}{2} \right]$$

$$\therefore V_{DS} = V_{DD} - I_D R_D$$

$$V_{DS} = V_{DD} - k_n R_D \left[ (V_{GS} - V_t) V_{DS} - \frac{V_{DS}^2}{2} \right]$$

$$\therefore V_{DS_C} = V_{DD} - k_n R_D \left[ (V_{GS_C} - V_t) V_{DS_C} - \frac{V_{DS_C}^2}{2} \right]$$

$$V_{DS_C} = 1.8 - 4 \times 17.5 \left[ (1.8 - 0.4) V_{DS_C} - \frac{V_{DS_C}^2}{2} \right]$$

$$V_{DS_C} = 1.8 - 70 \left[ 1.4 V_{DS_C} - \frac{V_{DS_C}^2}{2} \right]$$

$$V_{DS_C} = 1.8 - 98 V_{DS_C} + 35 V_{DS_C}^2$$

$$\therefore 35 V_{DS_C}^2 - 99 V_{DS_C} + 1.8 = 0$$

$$V_{DS_C} = \frac{+99 \pm \sqrt{99^2 - 4 \times 35 \times 1.8}}{2 \times 35}$$

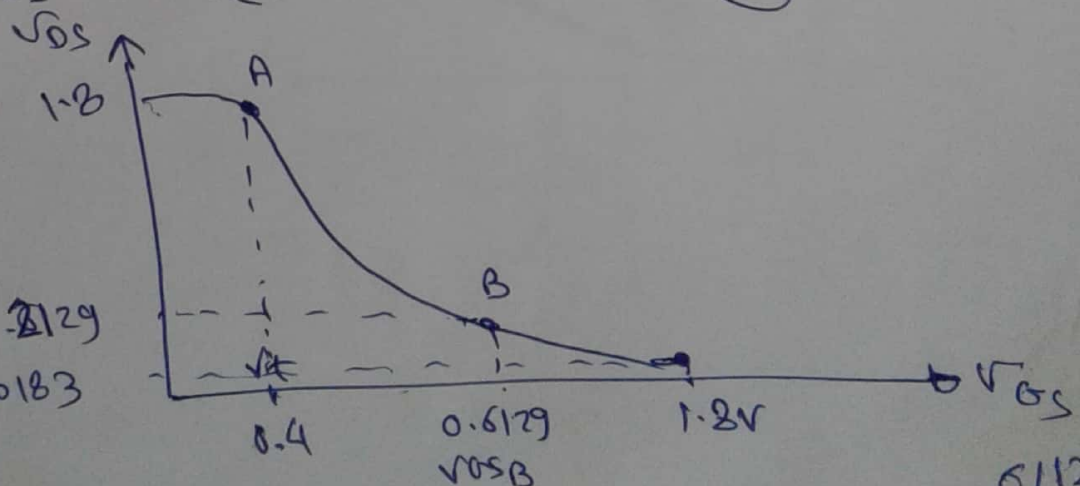
$$V_{DS_C} = 1.4142857 \pm 1.39598$$

$$V_{DS_C} < \begin{matrix} 2.81027 \text{ V } \times \times \\ 0.0183057 \text{ V } \checkmark \end{matrix}$$

because at triode  $V_{DS}$  very small

0.018,  $V_{GS}$  متعلق ہے کہ  $V_{GS}$  میں  $V_{DS_C}$  میں  $V_{GS}$  میں  $V_{GS}$  میں

$$\therefore V_{DS_C} = 0.018305 \text{ V } (\#)$$

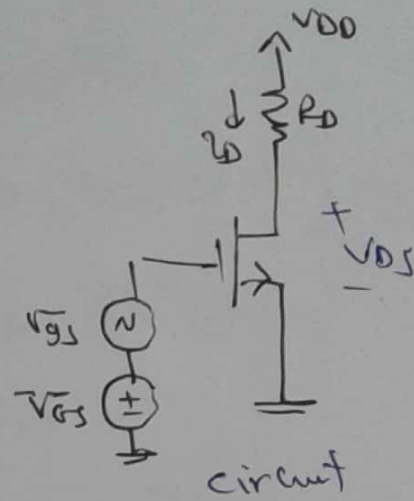
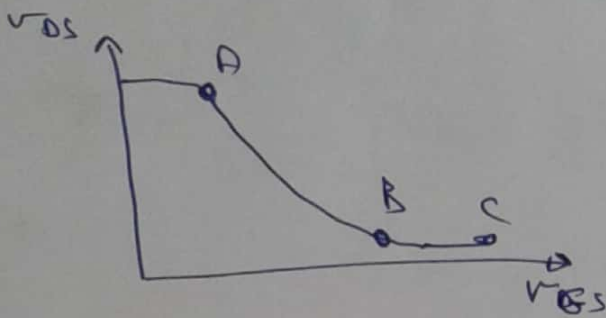


$$V_{GS_B} = 0.6129$$

$$V_{DS_C} = 0.0183$$

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# 7.1.9 Obtaining Linear Amplification by biasing the Transistor



From A  $\rightarrow$  B (sat)

$$I_D = \frac{1}{2} k_n (V_{GS} - V_t)^2$$

From circuit

$$v_{DS} = V_{DD} - I_D R_D$$

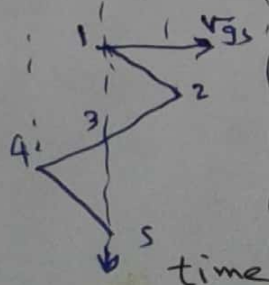
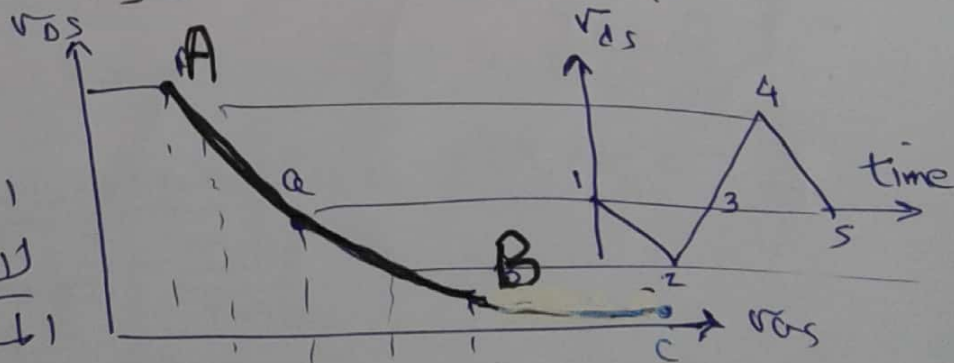
$$v_{DS} = V_{DD} - \frac{1}{2} k_n R_D (V_{GS} - V_t)^2$$

Since  $V_{GS} = V_{GS}^{DC} + v_{gs}^{AC}$

$$v_{GS}(t) = V_{GS}(t) + v_{gs}(t)$$

نقطة A تعبر نقطة Q-point وهي نقطة التشغيل المستقر  
 على منحنى  $I_D$  analysis ويجب ان تكون في المنطقة الخطية B-A  
 لتجنب التشوه (deformation) ac  $v_{gs}$  وهو

نقطة Q هي نقطة التشغيل المستقر  
 على منحنى  $I_D$  analysis ويجب ان تكون في المنطقة الخطية B-A  
 لتجنب التشوه (deformation) ac  $v_{gs}$  وهو





$$\therefore V_{DS} = V_{DD} - \frac{1}{2} k_n R_D (V_{GS} - V_T)^2$$

voltage gain  $A_V = \frac{\partial V_{DS}}{\partial V_{GS}} \downarrow V_{GS} = V_{GS}$

$$A_V = \frac{\partial}{\partial V_{GS}} \left[ V_{DD} - \frac{1}{2} k_n R_D (V_{GS} - V_T)^2 \right] \downarrow V_{GS} = V_{GS}$$

$$= 0 - \frac{1}{2} k_n R_D \times 2 (V_{GS} - V_T)$$

$$= -k_n R_D (V_{GS} - V_T)$$

$$\boxed{A_V = -k_n R_D V_{OV}} \quad \text{--- (1)}$$

### Remarks

(1) gain  $A_V \propto k_n, R_D, V_{OV}$

(2) gain is  $-ve$ , so o/p will have  $180^\circ$  phase shift with input

$$\boxed{(3) \left\{ A_V = \frac{O/P}{I/P} = \frac{V_{DS}}{V_{GS}} \right\}}$$

$$\therefore I_D = \frac{1}{2} k_n V_{OV}^2 \quad \text{--- (2)}$$

from (2)  $k_n V_{OV} = \frac{2I_D}{V_{OV}} = \frac{I_D}{V_{OV}/2}$

sub into eq (1)  $A_V = -k_n V_{OV} R_D = -\frac{2I_D \cdot R_D}{V_{OV}} = -\frac{I_D R_D}{V_{OV}/2}$

$$\boxed{A_V = -\frac{I_D R_D}{V_{OV}/2}} \quad \text{--- (3)}$$

نظراً لأننا نعلم أن  $I_D$  يعتمد على  $V_{GS}$  و  $R_D$  فمقدار  $A_V$  يعتمد على  $V_{GS}$

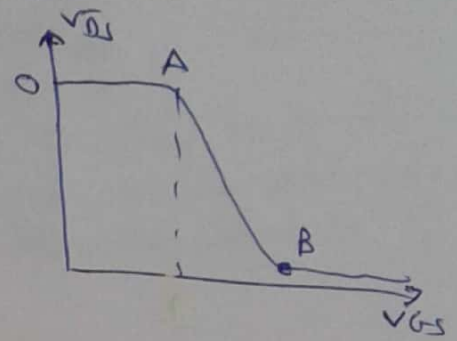
$$\therefore V_{DS} = V_{DD} - I_D R_D \quad \text{--- (4)}$$

$$= -I_D R_D = V_{GS} - V_{DD}$$

sub into (3)  $A_V = \frac{V_{DS} - V_{DD}}{V_{OV}/2} \quad \text{--- (5)}$

$$A_v = \frac{-I_D R_D}{v_{ov}/2} = - \frac{V_{DD} - V_{DS}}{v_{ov}/2} = -K_n R_D v_{ov} \quad (6)$$

عند نقطة A تكون من نقطة Q  
 ونقطة Q هي النقطة التي يكون فيها  
 gain هو الأكبر. لذا نقول  
 ان النقطة B هي النقطة التي يكون فيها  
 gain هو الأصغر. ونقول ان النقطة Q  
 هي نقطة الوسط بين A و B



$$\therefore A_v = - \frac{V_{DD} - V_{DS}}{v_{ov}/2}$$

$$A_{v \downarrow \text{max}} = - \frac{V_{DD} - V_{DSB}}{v_{ovB}/2}$$

$$|A_{v \text{max}}| = \frac{V_{DD} - V_{DSB}}{v_{ovB}/2}$$

Net Triode sat  $\Rightarrow$  النقطة B هي النقطة التي يكون فيها  
 $v_{DSB} = v_{GSB} - V_T$

$$\therefore |A_{v \text{max}}| = \frac{V_{DD} - v_{ovB}}{v_{ovB}/2} = 2 \frac{V_{DD} - v_{ovB}}{v_{ovB}}$$

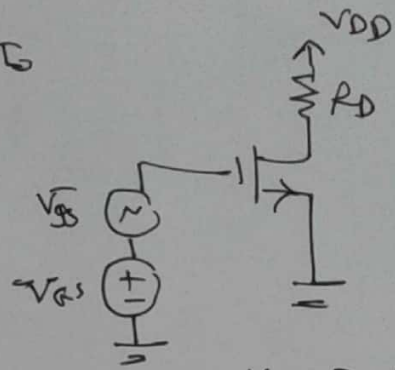
$\frac{1}{2} \text{max } @ \text{ } \bar{v}_Q$  ، (نقطة  $\bar{v}_Q$  هي النقطة التي يكون فيها)

$$\therefore v_{ovB} = v_{GSB} - V_T = \frac{\sqrt{2K_n R_D V_{DD} + 1} - 1}{K_n R_D}$$

To maximize the gain, the point Q must  
 be close as possible to point B  
 but the near to point B make a problem  
 of signal swing

EX) The Transistor is specified to have

$$\begin{aligned}
 V_t &= 0.4 \\
 K_n &= 0.4 \text{ mA/V}^2 \\
 W/L &= 10 \\
 \text{let } V_{DD} &= 1.8 \text{ V} \\
 R_D &= 17.5 \text{ k}\Omega \\
 V_{GS} &= 0.6 \text{ V}
 \end{aligned}$$



- (a) for  $v_{gs}=0$  (and hence  $v_{ds}=0$ ), find  $v_{ov}$ ,  $I_D$ ,  $v_{DS}$  &  $A_v$   
 (b) what is the maximum symmetrical signal swing allowed at the drain? Hence find the maximum allowable amplitude of a sinusoidal  $v_{gs}$ .

(a) since  $V_{GS} = 0.6 \text{ V}$

$$\therefore V_{ov} = V_{GS} - V_t = 0.6 - 0.4 = 0.2 \text{ V} \quad \#$$

assume  $\text{Tx}$  operates in saturation

$$\begin{aligned}
 I_D &= \frac{1}{2} K_n \frac{W}{L} (V_{GS} - V_t)^2 \\
 &= \frac{1}{2} K_n \frac{W}{L} V_{ov}^2 \\
 &= \frac{1}{2} \times 0.4 \frac{\text{mA}}{\text{V}^2} \times 10 \times 0.2^2
 \end{aligned}$$

$$I_D = 0.08 \text{ mA} \quad \# \checkmark$$

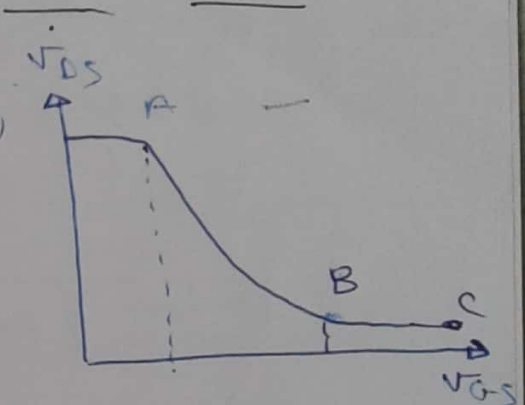
$$\begin{aligned}
 V_{DS} &= V_{DD} - I_D R_D \\
 &= 1.8 - 0.08 \times 17.5 = 0.4 \text{ V} \quad \# \checkmark
 \end{aligned}$$

check  $V_{DS} = 0.4$   
 $V_{GS} - V_t = V_{ov} = 0.2$  } so  $V_{DS} > V_{GS} - V_t$  sat  $\checkmark$

$$\begin{aligned}
 A_v &= -K_n V_{ov} R_D = -K_n \frac{W}{L} V_{ov} R_D \\
 &= -0.4 \times 10 \times 0.2 \times 17.5 = -14 \text{ V/V}
 \end{aligned}$$

$$A_v = \frac{-I_D R_D}{v_{gs}/2} = \frac{-0.08 \times 17.5}{0.2/2} = -14 \text{ V/V} \quad \# \checkmark$$

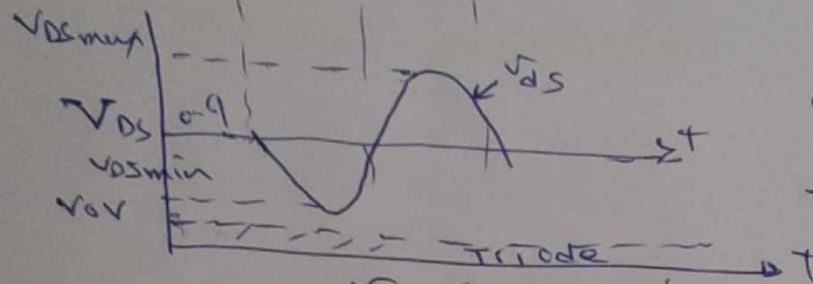
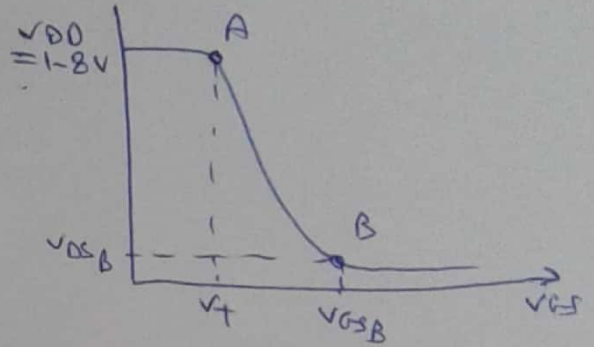
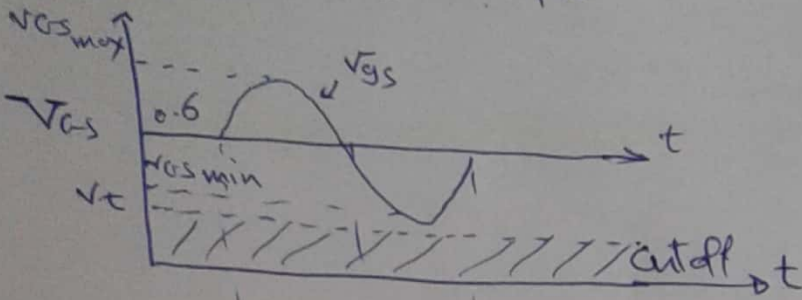
$$A_v = -\frac{V_{DD} - V_{DS}}{v_{gs}/2} = -\frac{1.8 - 0.4}{0.2/2} = -14 \text{ V/V}$$



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(b)

در این مدار کلاسیک



چون در نقطه A،  $V_{gs} = V_t$  و  $V_{ds} = 1.8V$  است  
 در نقطه B،  $V_{gs} = V_{gsB}$  و  $V_{ds} = V_{ov}$  است  
 در این ناحیه،  $V_{ds} < V_{gs} - V_t$  و ترانزیستور در ناحیه تریود عمل می‌کند.

در این مدار،  $V_{ds} < V_{gs} - V_t$  است.

$\therefore V_{ov} = 0.2 \quad V_{ds} = 0.4V$

$V_{ds} \text{ must be } = \pm (0.4 - 0.2) = \pm 0.2$

$\therefore |A_v| = \frac{V_{ds}}{V_{gs}}$

$V_{ds} = A_v V_{gs} \quad V_{gs} = \frac{V_{ds}}{A_v}$

$+14 = \frac{0.2}{V_{gs}}$

$\therefore V_{gs} = \frac{0.2}{14} = 14.285 \text{ mV} \quad \# \checkmark$

(DC level)  $V_{gs}$

for saturation

$V_{ds_{min}} \geq V_{gs_{max}} - V_t$

$V_{ds} - V_{ds} \geq V_{gs} + V_{gs} - V_t$

$0.4 - |A_v| V_{gs} \geq 0.6 + V_{gs} - 0.4$

$0.4 - |A_v| V_{gs} \geq 0.2 + V_{gs}$

$0.4 - 0.2 \geq V_{gs} (1 + |A_v|)$

$V_{gs} \leq \frac{0.2}{1 + |A_v|}$

$V_{gs} \leq \frac{0.2}{1 + 14} = 0.013333 \text{ V}$

این مقدار  $V_{gs}$  و  $V_{ds}$  در نقطه A و B در نمودار زیر مشخص شده است.



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$$\begin{aligned}
 V_{GSmax} &= V_{GS} + \hat{v}_{gs} \\
 &= 0.6 + 0.01333 \\
 V_{GSmax} &= 0.61333 \text{ mV} \quad (\#)
 \end{aligned}$$

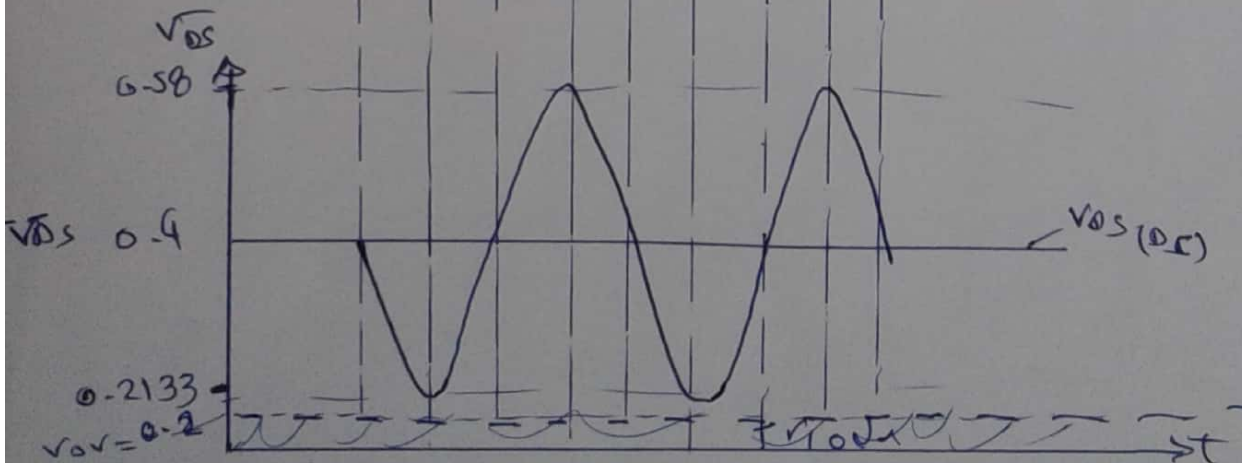
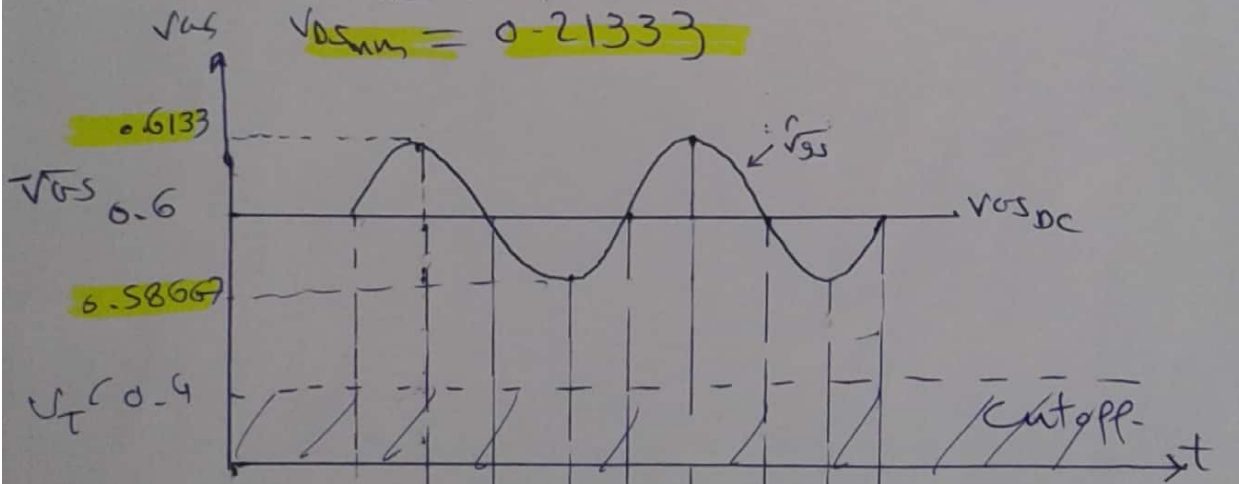
$$\begin{aligned}
 V_{GSmin} &= V_{GS} - \hat{v}_{gs} \\
 &= 0.6 - 0.01333 \\
 V_{GSmin} &= 0.58667 \text{ V} \quad (\#)
 \end{aligned}$$

$$\begin{aligned}
 V_{DSmax} &= V_{DS} + \hat{v}_{ds} \\
 &= V_{DS} + |A_v| v_{gs} \\
 &= 0.4 + 14 \times 0.01333
 \end{aligned}$$

$$V_{DSmax} = 0.58662$$

$$\begin{aligned}
 V_{DSmin} &= V_{DS} - \hat{v}_{ds} = V_{DS} - |A_v| v_{gs} \\
 &= 0.4 - 14 \times 0.01333
 \end{aligned}$$

$$V_{DSmin} = 0.21333$$



في هذا الرسم نرى ان الجهد  $V_{GS}$  يتذبذب حول قيمته المتوسطة  $V_{GS(DC)}$  و  $V_{DS}$  يتذبذب حول قيمته المتوسطة  $V_{DS(DC)}$  وهذا هو الشكل الطبيعي للإشارة في دائرة الترددات المنخفضة.

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